

Chung-Han Lin

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/11217857/publications.pdf>

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9

papers

106

citations

1478505

6

h-index

1588992

8

g-index

9

all docs

9

docs citations

9

times ranked

155

citing authors

#	ARTICLE	IF	CITATIONS
1	Neutron irradiation effects on metal-gallium nitride contacts. <i>Journal of Applied Physics</i> , 2014, 115, .	2.5	15
2	The effect of thermal reactor neutron irradiation on semi-insulating GaN. <i>Radiation Effects and Defects in Solids</i> , 2013, 168, 924-932.	1.2	6
3	Neutron irradiation effects on gallium nitride-based Schottky diodes. <i>Applied Physics Letters</i> , 2013, 103, .	3.3	23
4	Strain and Temperature Dependence of Defect Formation at AlGaN/GaN High-Electron-Mobility Transistors on a Nanometer Scale. <i>IEEE Transactions on Electron Devices</i> , 2012, 59, 2667-2674.	3.0	14
5	Field-induced strain degradation of AlGaN/GaN high electron mobility transistors on a nanometer scale. <i>Applied Physics Letters</i> , 2010, 97, .	3.3	9
6	Nanoscale mapping of temperature and defect evolution inside operating AlGaN/GaN high electron mobility transistors. <i>Applied Physics Letters</i> , 2009, 95, .	3.3	25
7	Observations of electrical and luminescence anomalies in InGaN ^x GaN blue light-emitting diodes. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2006, 24, 1016-1019.	2.1	3
8	Study of electroluminescence quenching in the InGaN/GaN blue diode with multi-quantum barrier structure. <i>Journal of Crystal Growth</i> , 2005, 278, 421-425.	1.5	11
9	Characterization of the carrier confinement for InGaN/GaN light emitting diode with multiquantum barriers. <i>Materials Research Society Symposia Proceedings</i> , 2004, 831, 406.	0.1	0